

# EFC8811R

## Power MOSFET for 1-Cell Lithium-ion Battery Protection 12V, 3.2mΩ, 27A, Dual N-Channel



ON Semiconductor®

www.onsemi.com

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-cell lithium-ion battery applications.

### Features

- 2.5V drive
- 2kV ESD HBM
- Common-Drain Type
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

### Applications

- 1-Cell Lithium-ion Battery Charging and Discharging Switch

### SPECIFICATIONS

#### ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V <sub>SSS</sub>	12	V
Gate to Source Voltage	V <sub>GSS</sub>	±8	V
Source Current (DC)	I <sub>S</sub>	27	A
Source Current (Pulse) PW≤100μs, duty cycle≤1%	I <sub>SP</sub>	100	A
Total Dissipation Surface mounted on ceramic substrate (5000mm <sup>2</sup> × 0.8mm)	P <sub>T</sub>	2.5	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

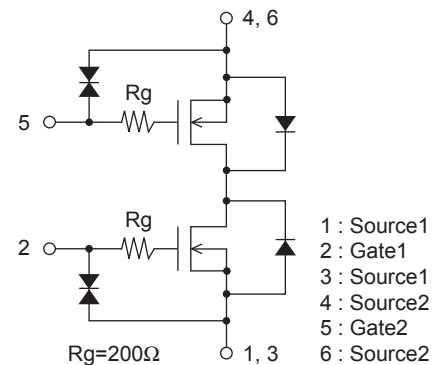
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient Surface mounted on ceramic substrate (5000mm <sup>2</sup> × 0.8mm)	R <sub>θJA</sub>	50	°C/W

V <sub>SSS</sub>	R <sub>SS(on)</sub> Max	I <sub>S</sub> Max
12V	3.2mΩ@ 4.5V	27A
	3.2mΩ@ 4.0V	
	3.2mΩ@ 3.8V	
	4.4mΩ@ 3.1V	
	6.3mΩ@ 2.5V	

### ELECTRICAL CONNECTION N-Channel



CSP6, 1.77x3.54 /  
EFCP3517-6DGH-020

### MARKING



### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

## EFC8811R

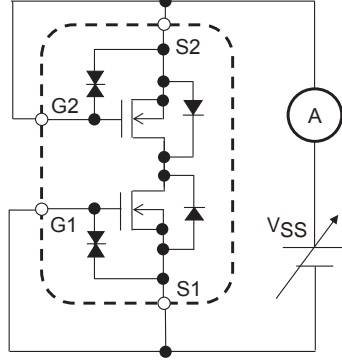
### ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Source to Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V Test Circuit 1	12			V
Zero-Gate Voltage Source Current	ISSS	VSS=10V, VGS=0V Test Circuit 1			1	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VSS=0V Test Circuit 2			±1	μA
Gate Threshold Voltage	VGS(th)	VSS=6V, IS=1mA Test Circuit 3	0.5		1.3	V
Forward Transconductance	gFS	VSS=6V, IS=3A Test Circuit 4		19		S
Static Source to Source On-State Resistance	RSS(on)1	IS=5A, VGS=4.5V Test Circuit 5	1.8	2.3	3.2	mΩ
	RSS(on)2	IS=5A, VGS=4.0V Test Circuit 5	1.9	2.4	3.2	mΩ
	RSS(on)3	IS=5A, VGS=3.8V Test Circuit 5	2.0	2.6	3.2	mΩ
	RSS(on)4	IS=5A, VGS=3.1V Test Circuit 5	2.1	3.3	4.4	mΩ
	RSS(on)5	IS=5A, VGS=2.5V Test Circuit 5	2.7	4.0	6.3	mΩ
Turn-ON Delay Time	td(on)	VSS=6V, VGS=4.5V, IS=3A Test Circuit 6		80		ns
Rise Time	tr			570		ns
Turn-OFF Delay Time	td(off)			38,000		ns
Fall Time	tf			17,700		ns
Total Gate Charge	Qg	VSS=6V, VGS=4.5V, IS=27A Test Circuit 7		100		nC
Forward Source to Source Voltage	VF(S-S)	IS=3A, VGS=0V Test Circuit 8		0.75	1.2	V

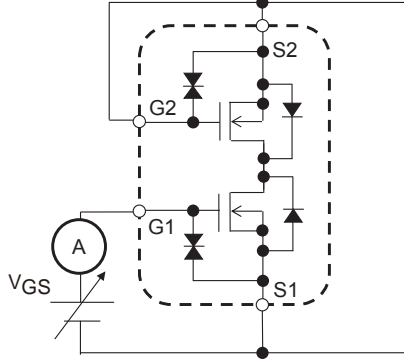
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Test circuits are example of measuring FET1 side

Test Circuit 1  
V<sub>SSS</sub> / I<sub>SSS</sub>

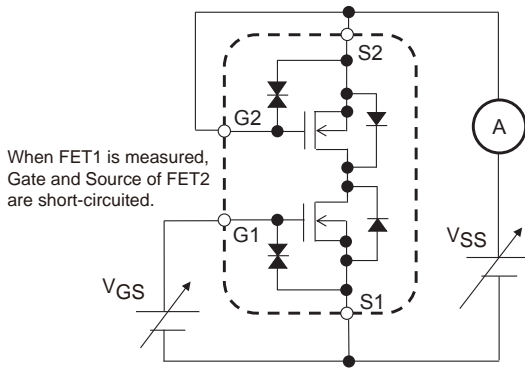


Test Circuit 2  
I<sub>GSS</sub>



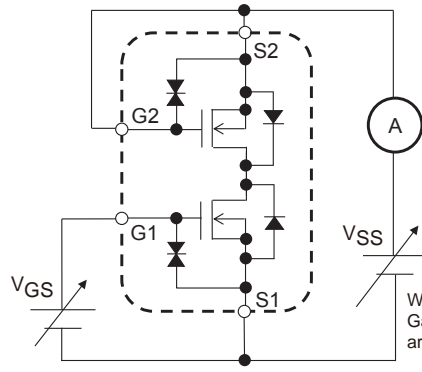
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3  
V<sub>GS(th)</sub>



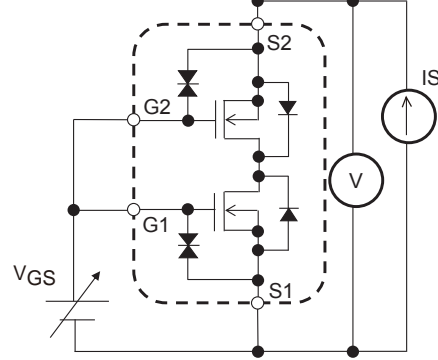
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4  
g<sub>FS</sub>

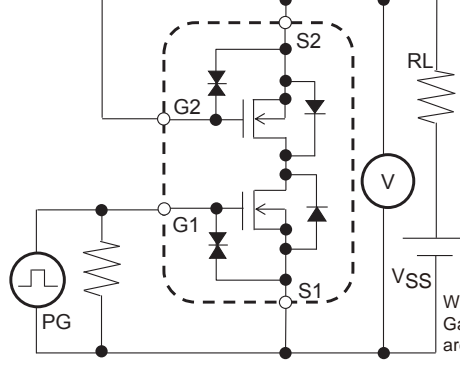


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5  
R<sub>SS(on)</sub>

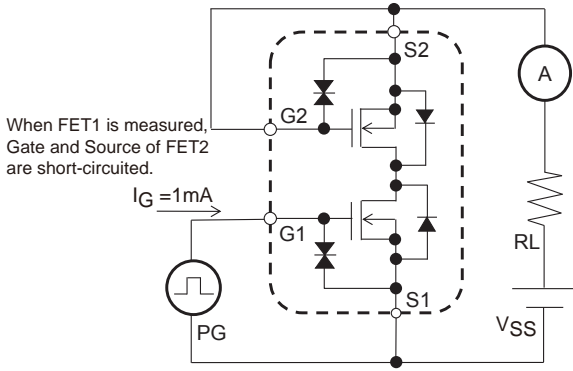


Test Circuit 6  
t<sub>d(on)</sub>, t<sub>r</sub>, t<sub>d(off)</sub>, t<sub>f</sub>



When FET1 is measured, Gate and Source of FET2 are short-circuited.

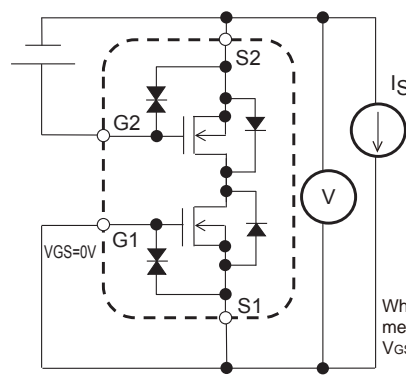
Test Circuit 7  
Q<sub>g</sub>



When FET1 is measured, Gate and Source of FET2 are short-circuited.

I<sub>G</sub> = 1mA

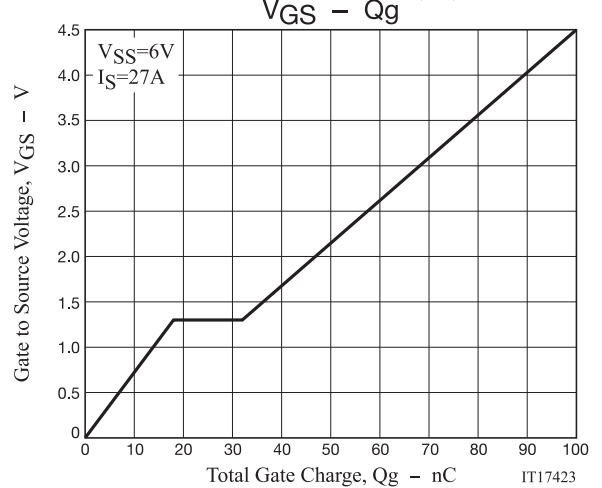
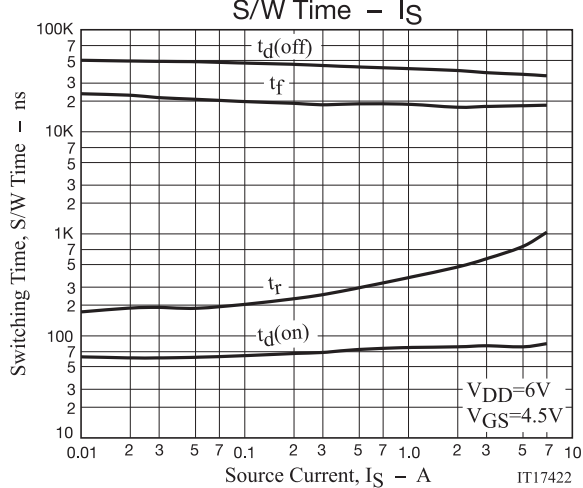
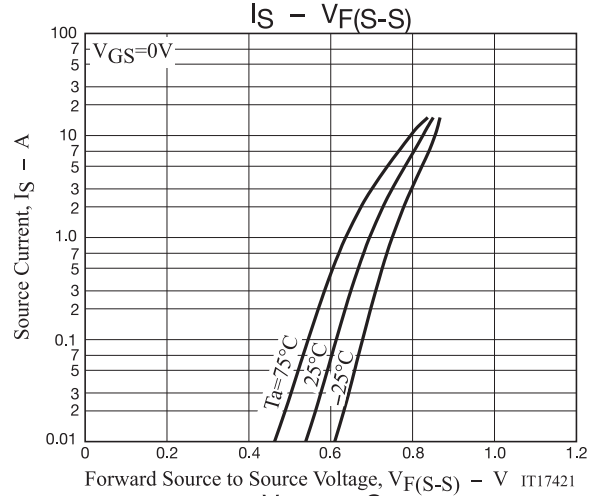
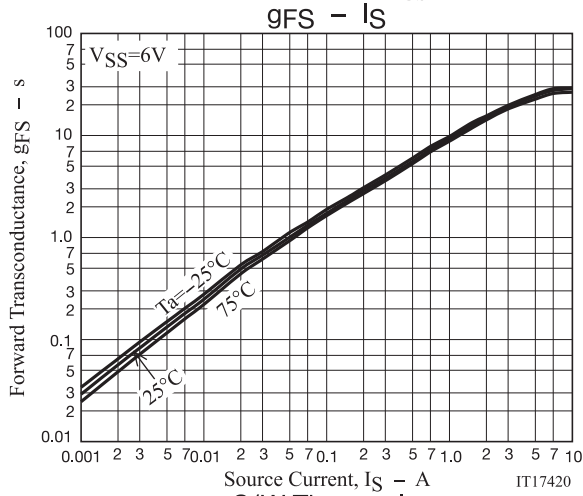
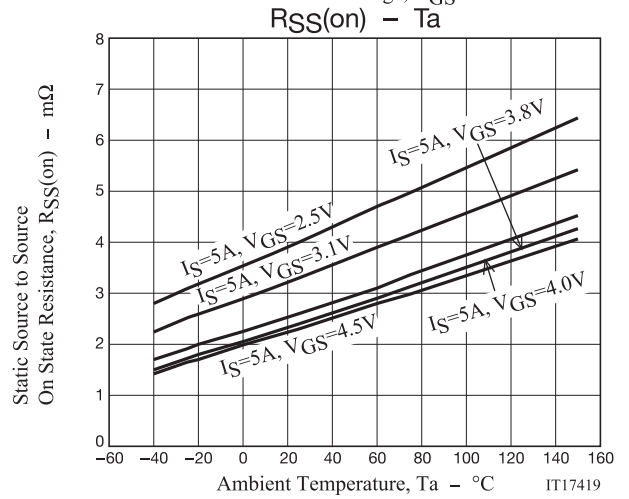
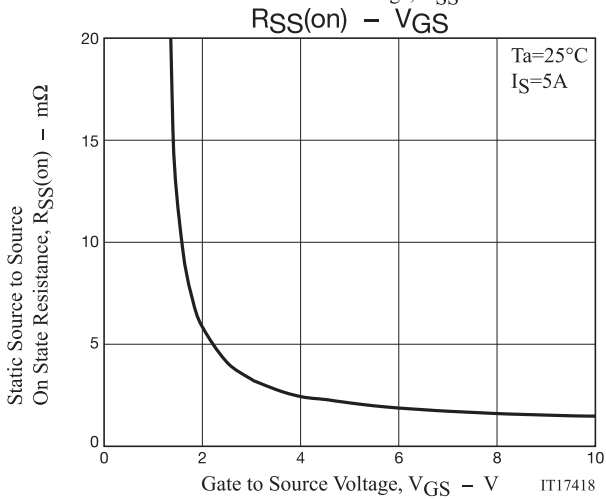
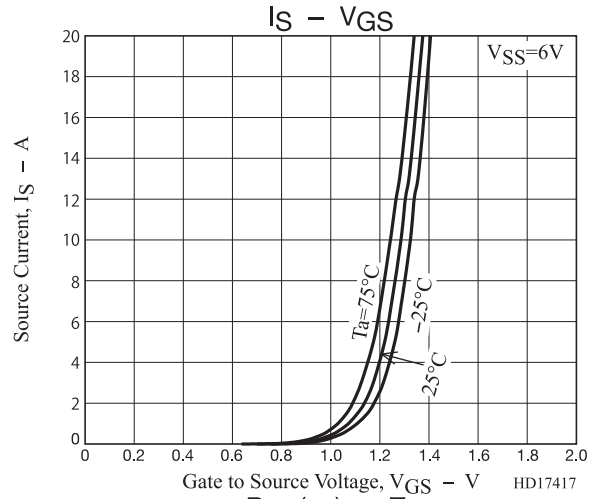
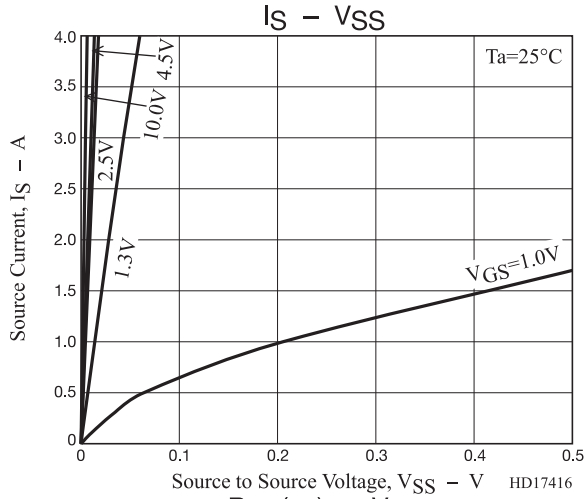
Test Circuit 8  
V<sub>F(S-S)</sub>



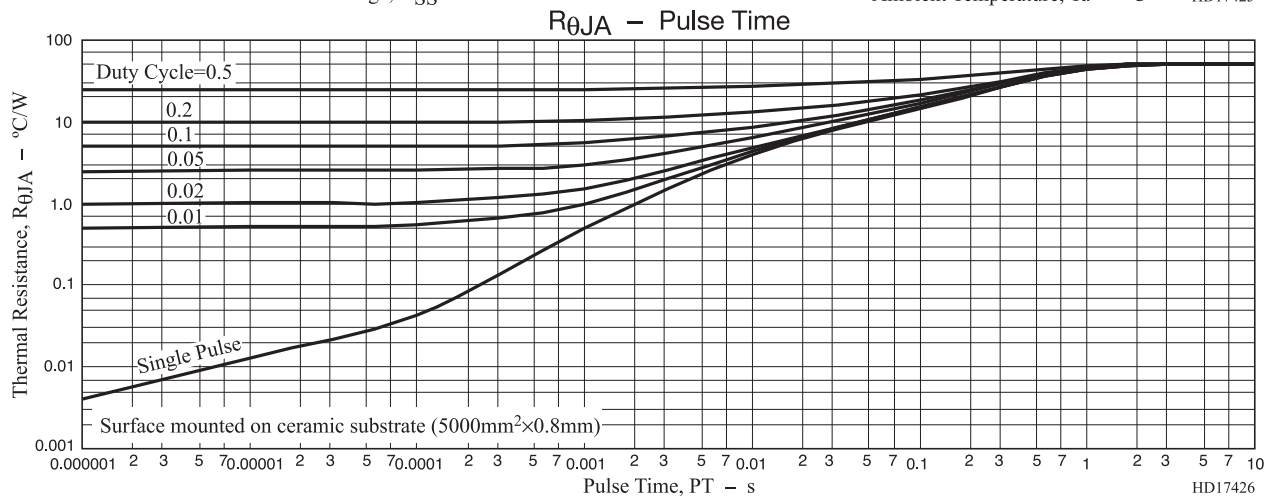
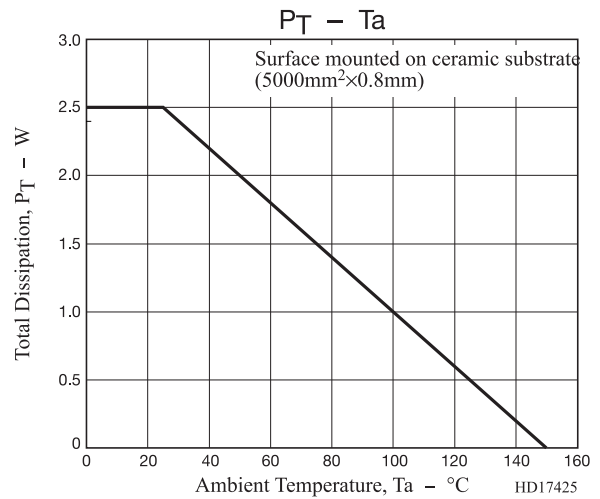
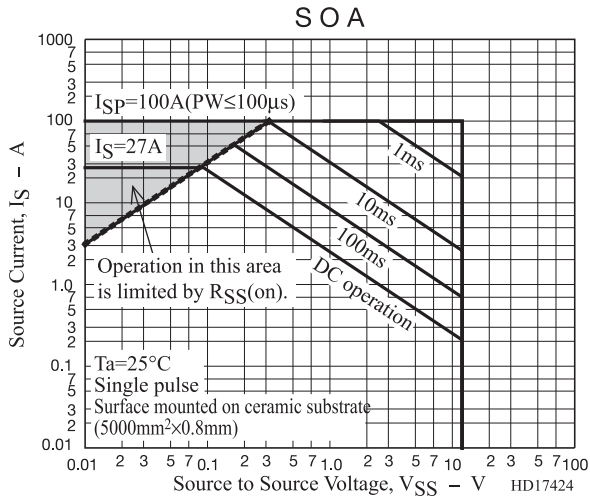
When FET1 is measured, +4.5V is added to V<sub>GS</sub> of FET2.

When FET2 is measured, the position of FET1 and FET2 is switched.

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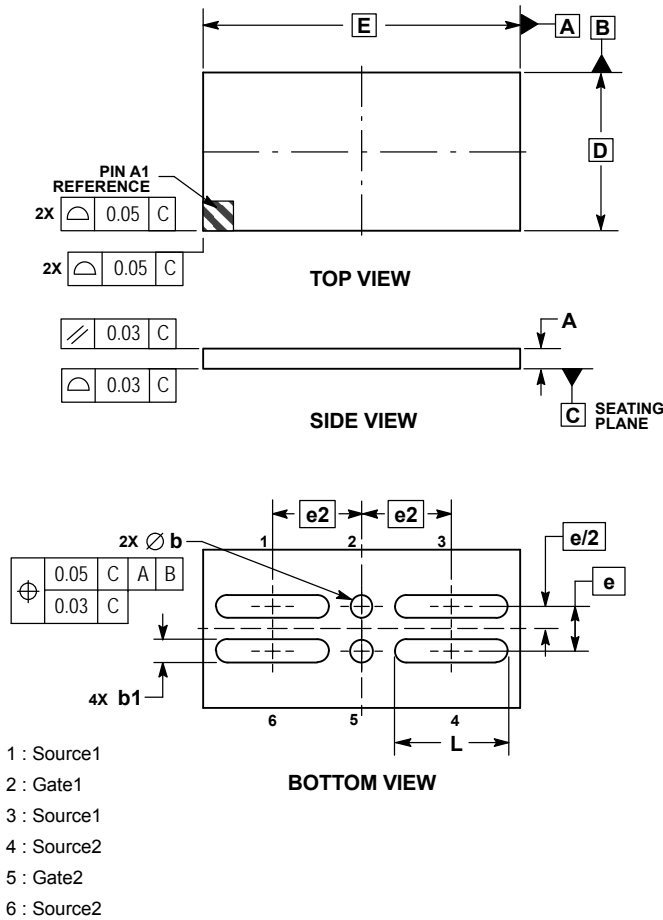
## PACKAGE DIMENSIONS

unit : mm

CSP6, 1.77x3.54 / EFCP3517-6DGH-020

CASE 568AL

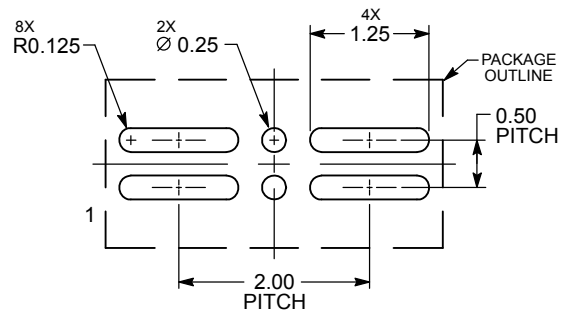
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- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	---	0.22
b	0.22	0.28
b1	0.22	0.28
D	1.77 BSC	
E	3.54 BSC	
e	0.50 BSC	
e2	1.00 BSC	
L	1.22	1.28

## RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
EFC8811R-TF	ML	CSP6, 1.77x3.54 / EFCP3517-6DGH-020 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. [http://www.onsemi.com/pub\\_link/Collateral/BRD8011-D.PDF](http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF)

Note on usage : Since the EFC8811R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact sales for use except the designated application.

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